

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-30. (Canceled)

31. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor.

32. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

33. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

34. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

35. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors.

36. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors,  
wherein the semiconductor device is flexible.

37. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid.

38. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid.

39. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors,  
wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

40. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a layer comprising resin covering the thin film transistors wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and wherein the crystalline silicon is formed by laser irradiation, wherein the semiconductor device is flexible.

41. (Withdrawn) A semiconductor device comprising:

a filmy substrate;

a thin film transistor formed over the filmy substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

42. (Withdrawn) A semiconductor device comprising:

a flexible substrate;

a thin film transistor formed over the flexible substrate with a resinous layer interposed therebetween;

a thin film transistor formed over the resinous layer; and

a silicon oxide film covering the thin film transistors, wherein the silicon oxide film is formed by applying a liquid,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

43.-46. (Canceled)

47. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor.

48. (Previously Presented) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

49. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

50. (Withdrawn) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

51. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a layer comprising resin covering the thin film transistor.

52. (Previously Presented) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a layer comprising resin covering the thin film transistor,  
wherein the semiconductor device is flexible.

53. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

54. (Withdrawn) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween, the thin film transistor having a channel forming region comprising crystalline silicon; and

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid.

55. (Withdrawn) A semiconductor device comprising:

a pair of filmy substrates opposing to each other;

a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween; and

a layer comprising resin covering the thin film transistor,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and

wherein the crystalline silicon is formed by laser irradiation.

56. (Previously Presented) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween; and

a layer comprising resin covering the thin film transistor,

wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and  
wherein the crystalline silicon is formed by laser irradiation,  
wherein the semiconductor device is flexible.

57. (Withdrawn) A semiconductor device comprising:  
a pair of filmy substrates opposing to each other;  
a thin film transistor formed between the pair of filmy substrates with a resinous layer interposed therebetween; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid,  
wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and  
wherein the crystalline silicon is formed by laser irradiation.

58. (Withdrawn) A semiconductor device comprising:  
a pair of flexible substrates opposing to each other;  
a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween; and  
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid,  
wherein the thin film transistor has a channel forming region comprising a crystalline silicon, and  
wherein the crystalline silicon is formed by laser irradiation.

59. (Withdrawn/Currently Amended) A semiconductor device according to claims [[27-34]] 31-34, wherein the silicon is amorphous silicon.



60. (Withdrawn/Currently Amended) A semiconductor device according to claims ~~[[27-34]]~~ 31-34, wherein the silicon is microcrystalline silicon.

61. (Currently Amended) A semiconductor device according to any one of claims ~~[[43-50]]~~ 47-50, wherein the silicon is amorphous silicon.

62. (Currently Amended) A semiconductor device according to any one of claims ~~[[43-50]]~~ 47-50, wherein the silicon is microcrystalline silicon.

63. (Currently Amended) A semiconductor device according to any one of claims 39-42 and 55-58, wherein the laser ~~[[light]]~~ comprises at least one selected from the group consisting of KrF excimer laser ~~[[light]]~~ and XeCl laser ~~[[light]]~~.

64. (Withdrawn/Currently Amended) A semiconductor device according to any one of claims ~~27, 29, 31, 33, 35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57~~, wherein the filmy substrate comprises a plastic substrate.

65. (Withdrawn/Currently Amended) A semiconductor device according to any one of claims ~~27, 29, 31, 33, 35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57~~, wherein the filmy substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

66. (Currently Amended) A semiconductor device according to any one of claims ~~28, 30, 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56 and 58~~, wherein the flexible substrate comprises a plastic substrate.

67. (Currently Amended) A semiconductor device according to any one of claims ~~28, 30, 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56~~ and 58, wherein the flexible substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

68. (Currently Amended) A semiconductor device according to any one of claims ~~[[31-58]]~~ 31-42 and 47-58, wherein the resinous layer comprises an acrylic resin.

69. (Currently Amended) A semiconductor device according to any one of claims ~~[[31-58]]~~ 31-42 and 47-58, wherein the resinous layer comprises at least one selected from the group consisting of methyl esters of acrylic acid, ethyl esters of acrylic acid, butyl esters of acrylic acid, and 2-ethylhexyl esters of acrylic acid.

70. (Currently Amended) A semiconductor device according to any one of claims ~~[[27-58]]~~ 31-42 and 47-58, wherein the thin film transistor comprises an inverted-staggered thin-film transistor.

71. (Currently Amended) A semiconductor device according to any one of claims ~~[[27-58]]~~ 31-42 and 47-58, wherein the thin film transistor comprises a coplanar thin-film transistor.

72.-84. (Canceled)